

Appn No. 10/698,360  
Amdt. Dated March 15, 2005  
Response to Office Action of February 24, 2005

2

**Amendments to the Specification:**

**At Page 1, line 1 is to be deleted.**

**At Page 1, line 4, a new paragraph entitled "Cross-References to Related Applications" is to be added, just below the Title, as follows:**

The present application is a continuation-in-part of US Application Serial No. 10/160,273 filed on June 4, 2002, now issued as US Patent No. 6,746,105, which is a continuation of US Application No. 09/112,767 filed on July 10, 1998, now issued as Patent No. 6,416,167, the entire contents of which are herein incorporated by reference.

**The second paragraph beginning at Page 9, lines 9-13, to be amended as follows:**

A portion of the diffusion barrier 24 extends from the silicon dioxide layer 18. An ink passivation layer in the form of a layer of silicon nitride 26 is positioned over the aluminum contact layers 20 and the silicon dioxide layer 18, as well as the diffusion barrier 24. Each portion of the layer 26 positioned over the contact layers has an opening 28 defined therein to provide access to the contacts ~~24~~20.

**The third paragraph beginning at Page 10, lines 11-16, to be amended as follows:**

A thermal actuator 68 is electrically connected to both the contact layers 20 at the openings 28. The openings 28 are positioned proximate one side 70 of the nozzle arrangement 10. The thermal actuator ~~60-68~~ is of titanium aluminum nitride (TiAlN). Further, the thermal actuator 68 has two anchor portions 72 that extend from the silicon nitride layer 26 to a predetermined point spaced from the silicon nitride layer 26. The anchor portions 72 are aligned transversely with respect to the substrate 14.